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IR-1609 (2-1941)

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

New York, New York

Daniel M. KINZER

Date: August 1, 2000

Serial No.: 09/292,186

Group Art Unit: 2811

Filed: April 15, 1999

Examiner: S. Hu

For: **P-CHANNEL TRENCH MOSFET STRUCTURE**Asst. Commissioner for Patents  
Washington, D.C. 20231RECEIVED  
AUG 21 2000  
TC 2800 MAIL ROOMAMENDMENT

Sir:

In response to the Office Action mailed June 6, 2000, please reconsider the above-identified application amended as follows:

IN THE CLAIMS:

Please cancel claims 14 and 15. Please amend the claims as follows:

*C1* *Sub D11* 1. (Amended) A trench-type power MOSFET having a vertical invertible channel of one of the [conductively] conductivity types disposed between a source region and a drain region; a gate oxide and gate contact thereon extending along the length of said invertible channel and operable to invert the conductivity type of said invertible channel; said gate contact containing a material of the other of the conductivity types; said vertical invertible channel having a constant concentration along its full length.

*C2* *Contd* *Sub D37* 4. (Amended) A power MOSFET comprising, in combination; a substrate of one of the conductivity types; an epitaxially deposited layer of the other conductivity type deposited atop said substrate and having a substantially constant concentration; a plurality of spaced trenches having vertical walls extending through said epitaxial layer; a thin gate oxide on